NCE N-Channel Super Trench Power MOSFET

Description

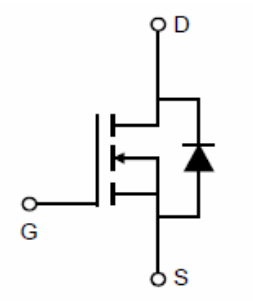
The NCEP30T17GU uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and Q_g. This device is ideal for high-frequency switching and synchronous rectification.

General Features

- V_{DS} =30V,I_D =170A
  $R_{DS(ON)}$=0.97mΩ (typical) @ V_{GS}=10V
  $R_{DS(ON)}$=1.25mΩ (typical) @ V_{GS}=4.5V
- Excellent gate charge x $R_{DS(on)}$ product(FOM)
- Very low on-resistance $R_{DS(on)}$
- 150 °C operating temperature
- Pb-free lead plating
- 100% UIS tested

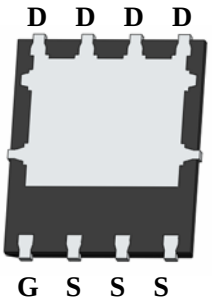
Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification



Schematic Diagram

Top View



Bottom View

100% UIS TESTED!

100% ΔVds TESTED!

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
P30T17GU	NCEP30T17GU	DFN5X6-8L	-	-	-

Absolute Maximum Ratings (T_C=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	±20	V
Drain Current-Continuous **(Silicon Limited)**	I_D	170	A
Drain Current-Continuous(T_C=100℃)	I_D (100℃)	120	A
Pulsed Drain Current **(Package Limited)**	I_{DM}	400	A
Maximum Power Dissipation	P_D	88	W
Derating factor		0.70	W/℃
Single pulse avalanche energy (Note 5)	E_{AS}	1350	mJ
Operating Junction and Storage Temperature Range	T_J,T_{STG}	-55 To 150	℃

Thermal Characteristic

Thermal Resistance,Junction-to-Case (Note 2)	$R_{\theta JC}$	1.42	℃/W
Thermal Resistance,Junction-to-Ambient (Note 2)	$R_{\theta JA}$	50	℃/W

Electrical Characteristics (T_C=25℃unless otherwise noted)

Parameter	Symbol		Condition	Min	Typ	Max	Unit
Off Characteristics							
Drain-Source Breakdown Voltage	BV_{DSS}		V_{GS}=0V I_D=250μA	30		-	V
Zero Gate Voltage Drain Current	I_{DSS}	T_J=25℃	V_{DS}=30V,V_{GS}=0V	-	-	1	μA
		T_J=55℃		-	-	1.5	μA
Gate-Body Leakage Current	I_{GSS}		V_{GS}=±5V,V_{DS}=0V	-	-	±80	nA
			V_{GS}=±20V,V_{DS}=0V	-	-	±100	nA
On Characteristics (Note 3)							
Gate Threshold Voltage	$V_{GS(th)}$		V_{DS}=V_{GS},I_D=250μA	1.0	1.5	2.0	V
Drain-Source On-State Resistance	$R_{DS(ON)}$		V_{GS}=10V, I_D=20A	0.75	0.97	1.2	mΩ
			V_{GS}=4.5V, I_D=20A	1	1.25	1.5	mΩ
Gate resistance	R_G		F=1.0MHz	-	4.0	-	Ω
Forward Transconductance	g_{FS}		V_{DS}=5V,I_D=20A		80	-	S
Dynamic Characteristics (Note4)							
Input Capacitance	C_{lss}		V_{DS}=15V,V_{GS}=0V, F=1.0MHz	-	5300	6890	PF
Output Capacitance	C_{oss}			-	1800	2600	PF
Reverse Transfer Capacitance	C_{rss}			-	100	200	PF
Switching Characteristics (Note 4)							
Turn-on Delay Time	$t_{d(on)}$		V_{DD}=15V,I_D=20A V_{GS}=10V,R_G=1.6Ω	-	12	-	nS
Turn-on Rise Time	t_r			-	6.5	-	nS
Turn-Off Delay Time	$t_{d(off)}$			-	48	-	nS
Turn-Off Fall Time	t_f			-	7.5	-	nS
Total Gate Charge	Q_g		V_{DS}=15V,I_D=20A, V_{GS}=10V	-	90	126	nC
Gate-Source Charge	Q_{gs}			-	12	18	nC
Gate-Drain Charge	Q_{gd}			-	13	19.5	nC
Drain-Source Diode Characteristics							
Diode Forward Voltage (Note 3)	V_{SD}		V_{GS}=0V,I_S=20A	-	-	1.2	V
Diode Forward Current (Note 2)	I_S			-	-	170	A
Reverse Recovery Time	t_{rr}		T_J = 25°C, I_F = I_S di/dt = 100A/μs (Note3)	-	-	30	nS
Reverse Recovery Charge	Qrr			-	-	110	nC

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. The value of $R_{\theta JA}$ is measured with the device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A =25° C. the maximum allowed junction temperature of 150°C. The value in any given application depends on the user's specific board design.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production
5. E_{AS} condition : Tj=25℃,V_{DD}=20V,V_G=10V,L=0.5mH,Rg=25Ω

Typical Electrical and Thermal Characteristics

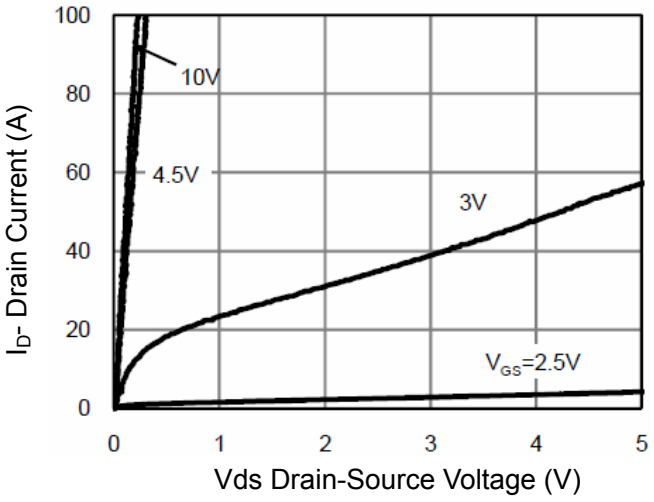


Figure 1 Output Characteristics

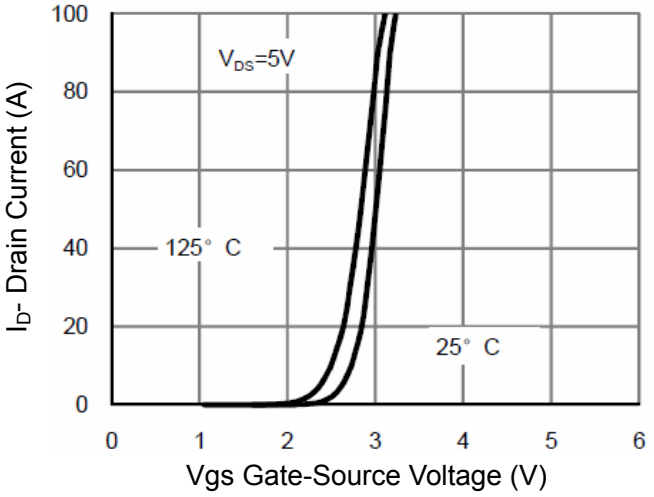


Figure 2 Transfer Characteristics

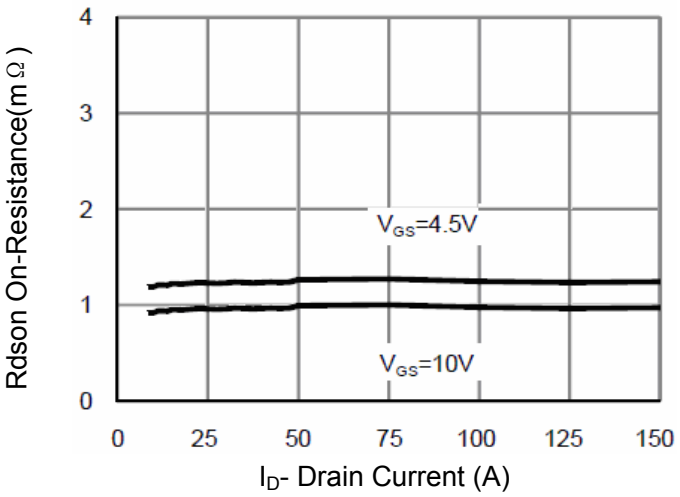


Figure 3 Rdson- Drain Current

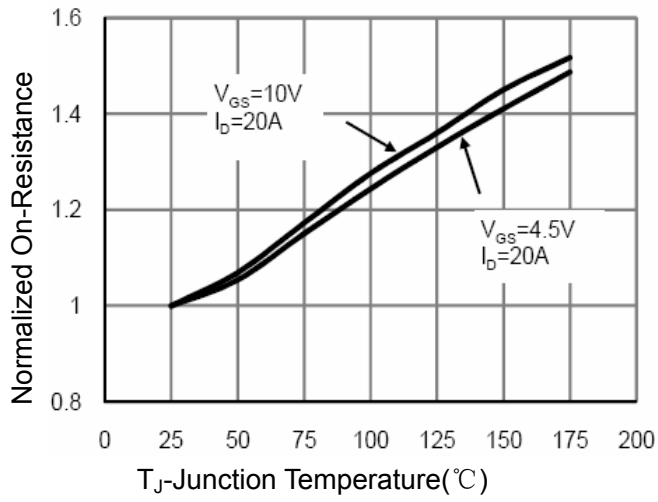


Figure 4 Rdson-Junction Temperature

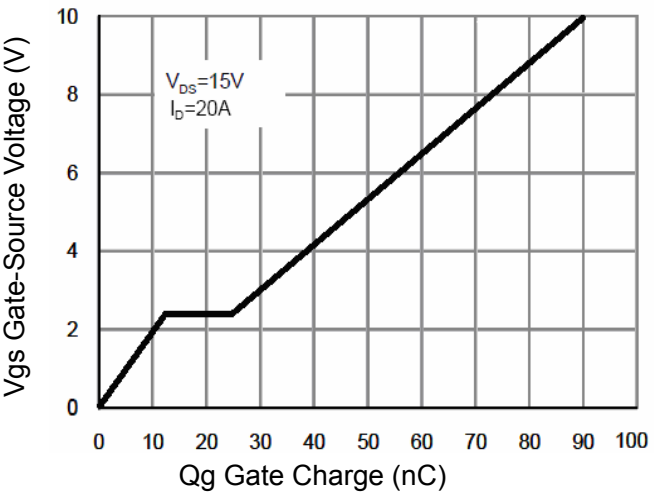


Figure 5 Gate Charge

Figure 6 Source- Drain Diode Forward

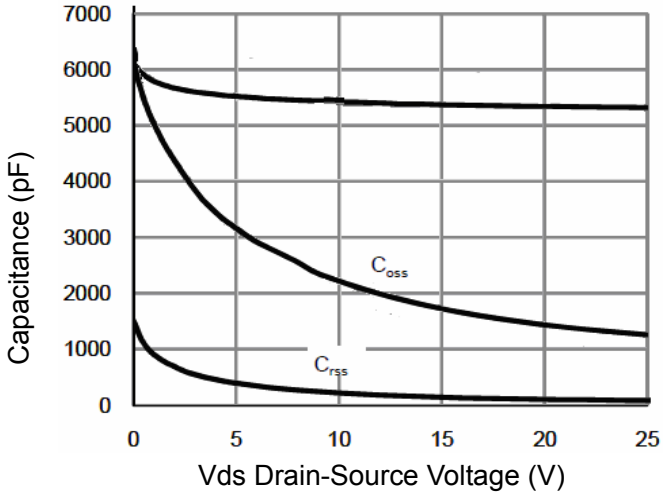


Figure 7 Capacitance vs Vds

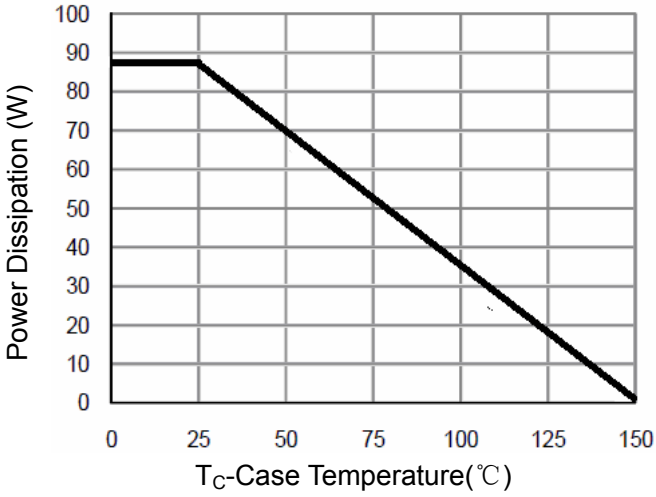


Figure 9 Power De-rating

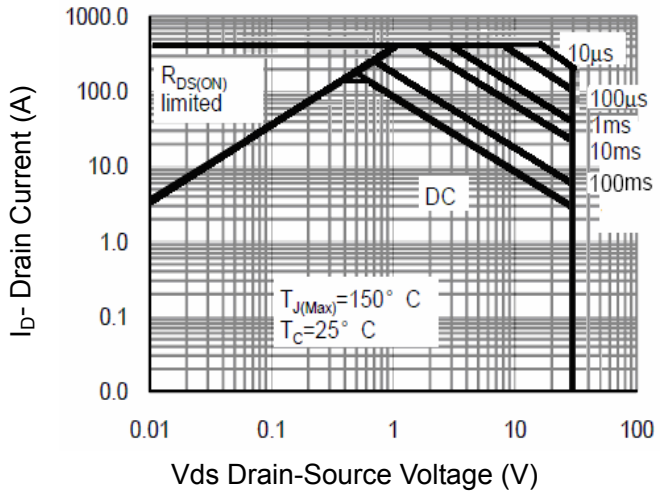


Figure 8 Safe Operation Area

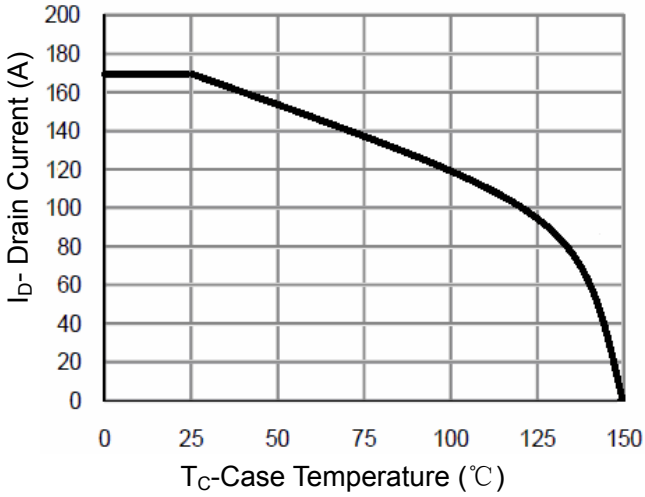


Figure 10 Current De-rating

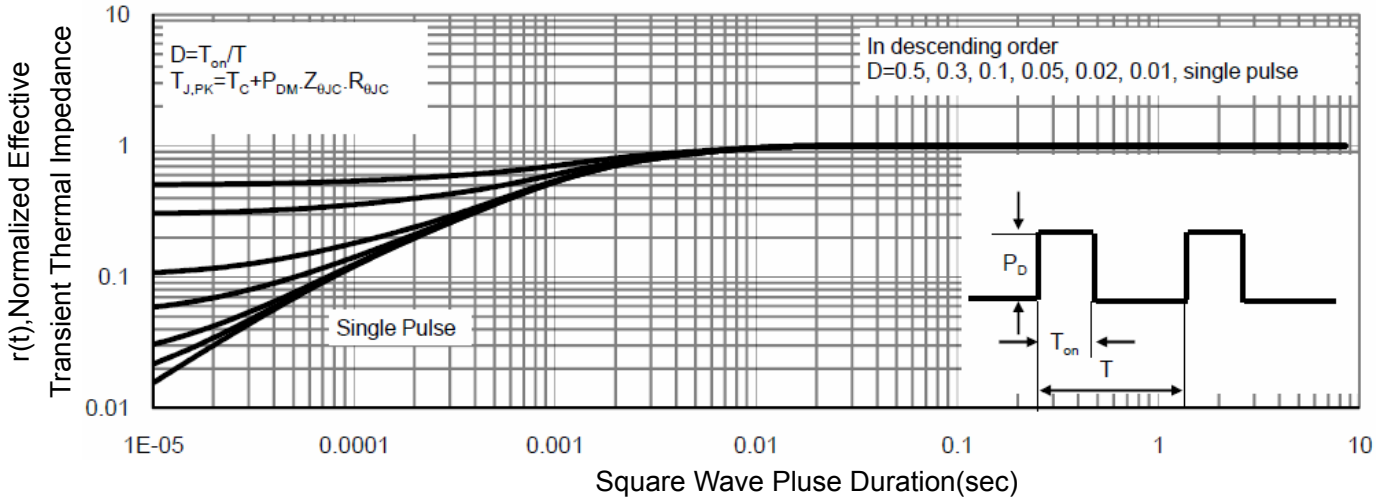
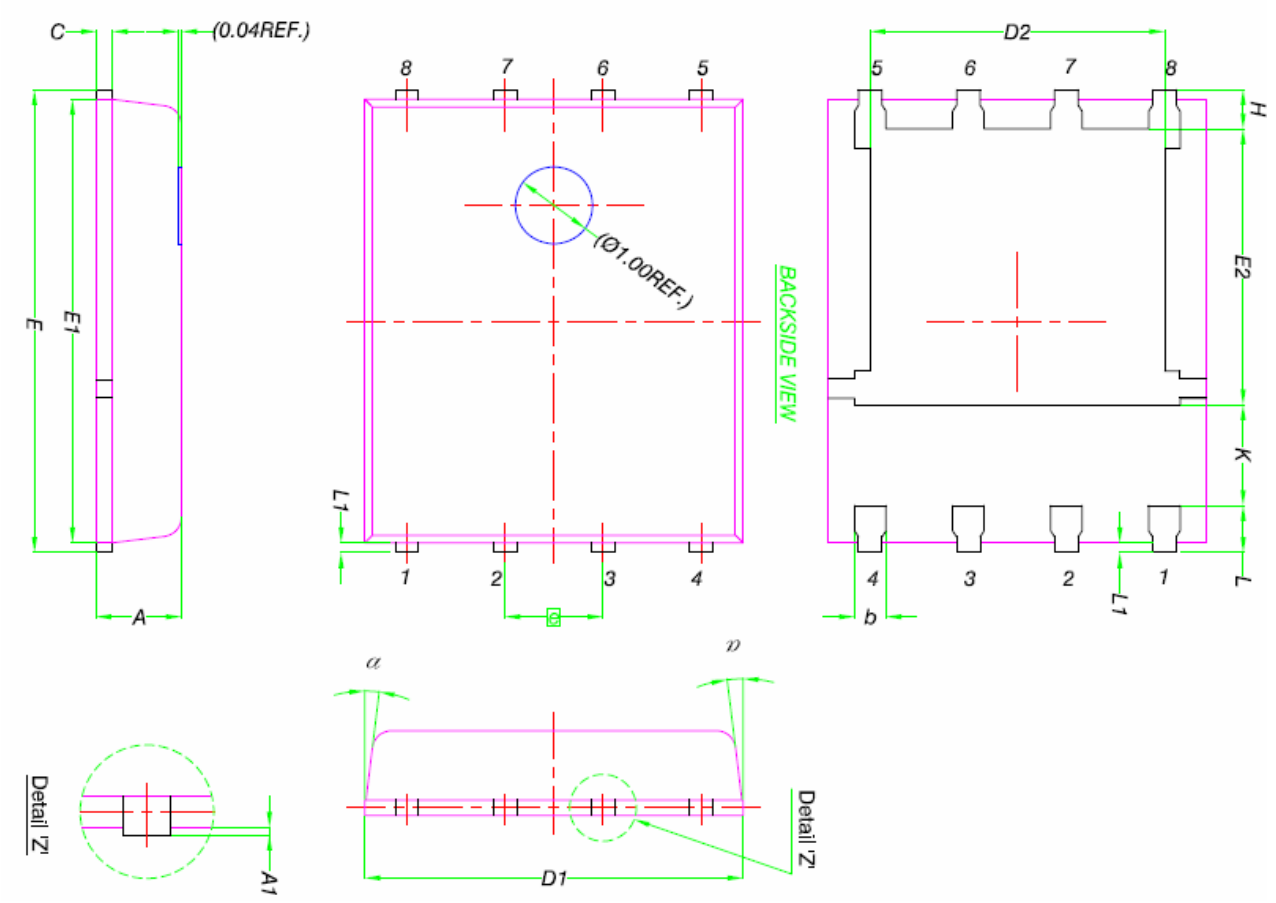
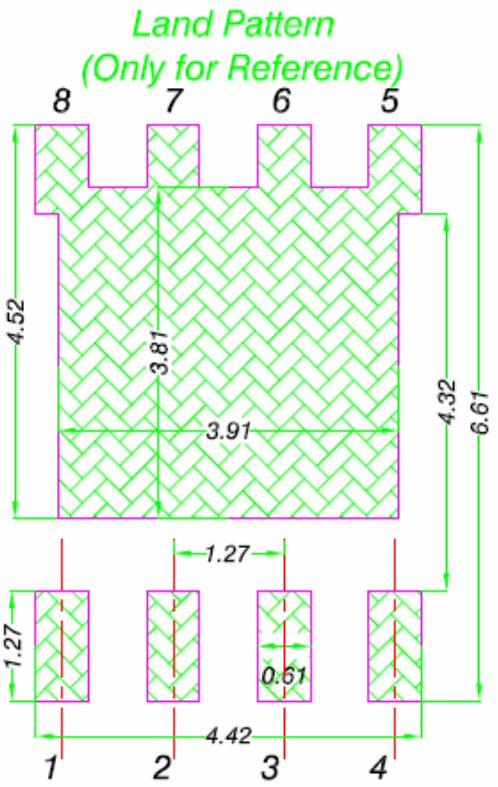


Figure 11 Normalized Maximum Transient Thermal Impedance

DFN5X6-8L Package Information



DIM.	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.90	1.00	1.10
A1	0	-	0.05
b	0.33	0.41	0.51
C	0.20	0.25	0.30
D1	4.80	4.90	5.00
D2	3.61	3.81	3.96
E	5.90	6.00	6.10
E1	5.70	5.75	5.80
E2	3.38	3.58	3.78
e	1.27 BSC		
H	0.41	0.51	0.61
K	1.10	-	-
L	0.51	0.61	0.71
L1	0.06	0.13	0.20
α	0°	-	12°



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